

P D Yoder

List of Publications by Year in descending order

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20
papers

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citations

1040056

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20
times ranked

346
citing authors

#	ARTICLE	IF	CITATIONS
1	Efficiency droop due to electron spill-over and limited hole injection in III-nitride visible light-emitting diodes employing lattice-matched InAlN electron blocking layers. Applied Physics Letters, 2012, 101, .	3.3	80
2	Abinitioanalysis of the electronâ€phonon interaction in silicon. Journal of Applied Physics, 1993, 73, 4378-4383.	2.5	52
3	Monte Carlo simulation of hot electron transport in Si using a unified pseudopotential description of the crystal. Semiconductor Science and Technology, 1992, 7, B357-B359.	2.0	33
4	Electrothermal analysis of AlGaIn/GaN high electron mobility transistors. Journal of Computational Electronics, 2008, 7, 236-239.	2.5	32
5	Geiger-Mode Operation of GaN Avalanche Photodiodes Grown on GaN Substrates. IEEE Photonics Technology Letters, 2009, 21, 1526-1528.	2.5	27
6	First-principles Monte Carlo simulation of transport in Si. Semiconductor Science and Technology, 1994, 9, 852-854.	2.0	20
7	â€œHot electrons in Si lose energy mostly to optical phononsâ€ Truth or myth?. Applied Physics Letters, 2019, 114, 222104.	3.3	15
8	AlGaIn-Based Vertical Injection Laser Diodes Using Inverse Tapered p-Waveguide for Efficient Hole Transport. IEEE Journal of Quantum Electronics, 2014, 50, 166-173.	1.9	14
9	Anisotropic Transient and Stationary Electron Velocity in Bulk Wurtzite GaN. IEEE Electron Device Letters, 2008, 29, 1190-1192.	3.9	12
10	A High-Linearity Modified Uni-Traveling Carrier Photodiode With Offset Effects of Nonlinear Capacitance. Journal of Lightwave Technology, 2009, 27, 4435-4439.	4.6	9
11	Temperature- and Doping-Dependent Anisotropic Stationary Electron Velocity in Wurtzite GaN. IEEE Electron Device Letters, 2011, 32, 1522-1524.	3.9	9
12	Nitride band-structure model in a quantum well laser simulator. Optical and Quantum Electronics, 2008, 40, 295-299.	3.3	6
13	Luminescence spectra of an Alâ€SiO2â€p-Si tunnel metal-oxide-semiconductor structure. Journal of Applied Physics, 2005, 98, 083511.	2.5	4
14	Soft Error Trends and New Physical Model for Ionizing Dose Effects in Double Gate Z-RAM Cell. IEEE Transactions on Nuclear Science, 2007, 54, 2363-2370.	2.0	4
15	Geiger mode simulation of GaN homojunction avalanche photodetectors. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S662.	0.8	4
16	Traveling dipole domains in AlGaIn/GaN heterostructures and the direct generation of millimeterâ€wave oscillations. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2285-2287.	0.8	4
17	The influence of nonlinear capacitance and responsivity on the linearity of a modified uni-traveling carrier photodiode. , 2008, , .		3
18	PERFORMANCE ENHANCEMENT OF InGaIn-BASED LASER DIODES USING A STEP-GRADED Al_xGa_{1-x}N ELECTRON BLOCKING LAYER. International Journal of High Speed Electronics and Systems, 2011, 20, 515-520.	0.7	3

#	ARTICLE	IF	CITATIONS
19	Full-Band Monte Carlo Transport Calculation in an Integrated Simulation Platform. , 1995, , 400-403.		3
20	Bandwidth and Charge Balancing of Partially Depleted Absorber Photodiodes. IEEE Journal of Quantum Electronics, 2007, 43, 992-997.	1.9	1